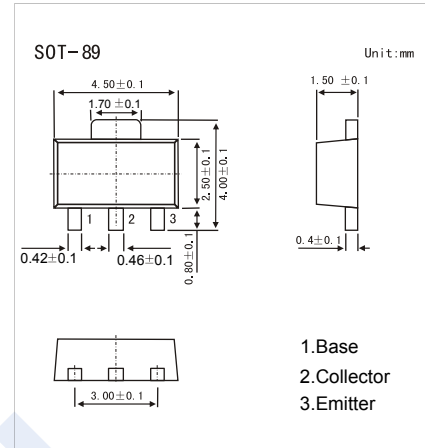


NPN Transistors

CXT5551 (KXT5551)

■ Features

- High current (max. 600mA).
- Low voltage (max. 160 V).
- Complementary to CXT5401



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	180	V
Collector - Emitter Voltage	V _{CE0}	160	
Emitter - Base Voltage	V _{EB0}	6	
Collector Current - Continuous	I _c	600	mA
Collector Power Dissipation	P _c	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 100 μA, I _E = 0	180			V
Collector- emitter breakdown voltage	V _{CE0}	I _c =1 mA, I _B = 0	160			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _c = 0	6			
Collector-base cut-off current	I _{CB0}	V _{CB} = 120 V, I _E = 0			50	nA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _c =0			50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =10 mA, I _B =1mA			0.15	V
		I _c =50 mA, I _B =5mA			0.2	
Base - emitter saturation voltage	V _{BE(sat)}	I _c =10 mA, I _B =1mA			1	
		I _c =50 mA, I _B =5mA			1	
DC current gain	h _{FE}	V _{CE} = 5V, I _c = 1mA	80			
		V _{CE} = 5V, I _c = 10mA	80		300	
		V _{CE} = 5V, I _c = 50mA	30			
Noise figure	NF	V _{CE} =5V, I _c =0.2mA, f=10Hz to 15.7KHZ, R _s =10Ω			8	dB
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E =0, f=1MHz			6	pF
Transition frequency	f _T	V _{CE} = 10V, I _c = 10mA, f=100MHz	100			MHz

■ Marking

Marking	5551
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NPN Transistors

CXT5551 (KXT5551)

Typical Characteristics

